**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- · High blocking voltage capability
- High noise immunity suitable for noisy applications
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

# 3. Applications

- General purpose low power motor control
- General purpose switching and phase control

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Absolute	maximum rating					
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>sp</sub> ≤ 108 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	10	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	-	11	Α
T <sub>j</sub>	junction temperature		-	-	125	°C
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_i = 25 \text{ °C; } Fig. 9$	-	30	70	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	Static characteristics						
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	5	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 2 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>		-	1.2	1.5	V
Dynamic characteristics							
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit		100	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; dI_{com}/dt = 1.8 \text{ A/}$ ms; $I_T = 1 \text{ A};$ gate open circuit		-	50	-	V/µs

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2	4	T2—T1
3	G	gate		sym051
4	T2	main terminal 2	1 2 3	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT134W-600	SOT223	BT134W-600,115	Reel	1000	SOT223	16-Mar-2006
		BT134W-600,135	Reel	4000		

# 7. Marking

### Table 4. Marking codes

Table It marking course					
Order number	Marking codes				
	Assembly factory: L	Assembly factory: d			
BT134W-600,115	JLxxx 60 BT134W	Jdxxx 60 BT134W			
BT134W-600,135	JLxxx 60 BT134W	-			

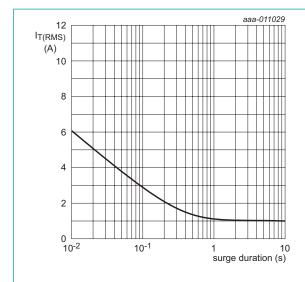
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# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 108$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	10	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	11	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	0.5	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 0.2 A	-	50	A/µs
	current		-	50	A/µs
			-	50	A/µs
			-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



f = 50 Hz; T<sub>sp</sub> ≤ 108 °C Fig. 1. RMS on-state current as a function of surge duration; maximum values

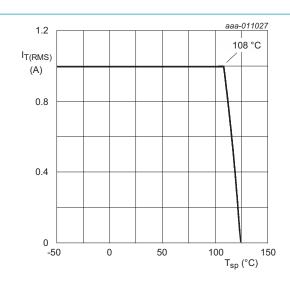
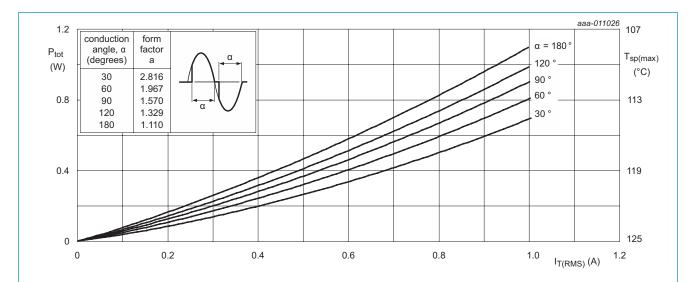


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

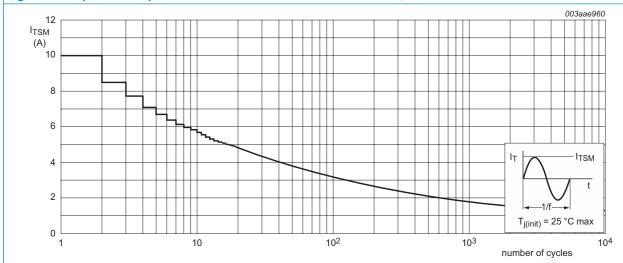
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 $\alpha$  = conduction angle

a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

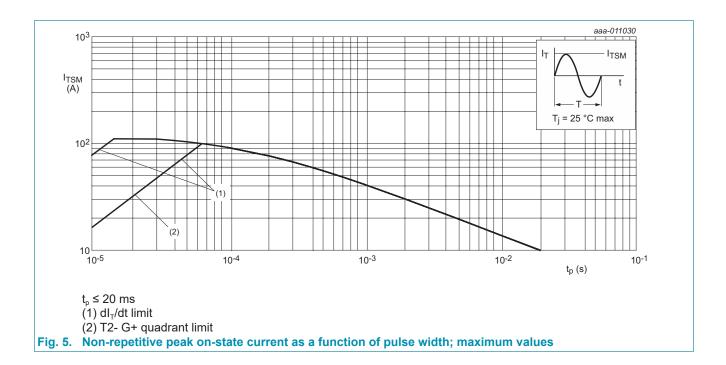
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-sp)}}$	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
ambient free air		full cycle; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W

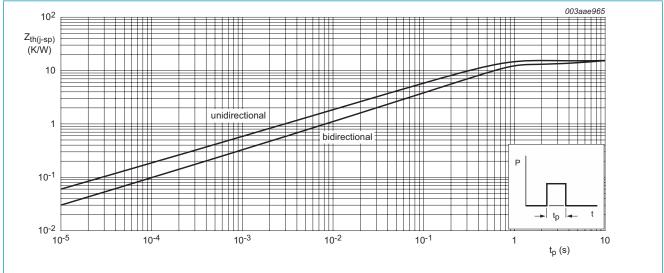
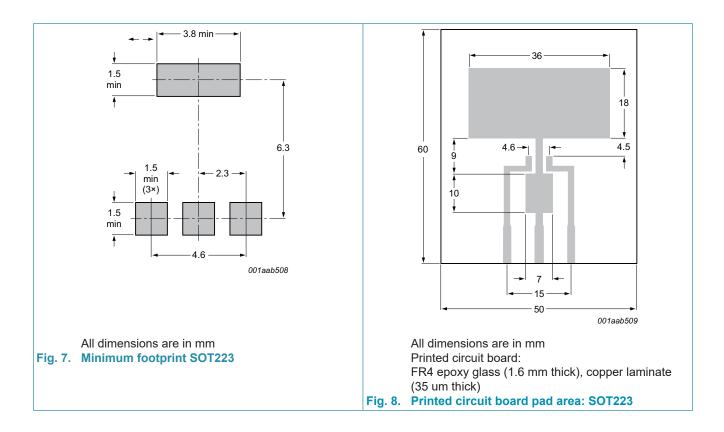


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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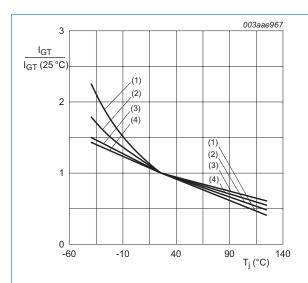


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## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		·			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 9}}$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	30	70	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	7	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	16	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. } \underline{10}$	-	5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. } 10$	-	7	30	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	5	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 2 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 13	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; dl_{com}/dt = 1.8 \text{ A/}$ ms; $I_T = 1 \text{ A};$ gate open circuit	-	50	-	V/µs
$\mathbf{t}_{\mathrm{gt}}$	gate-controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs





<sup>(2)</sup> T2- G-

(4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

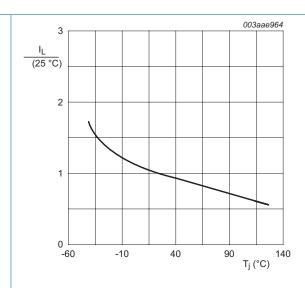


Fig. 10. Normalized latching current as a function of junction temperature

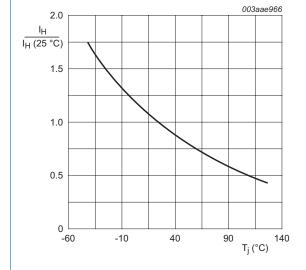
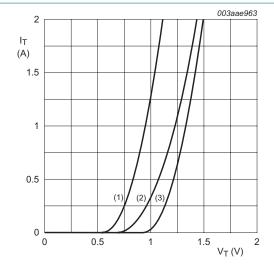


Fig. 11. Normalized holding current as a function of junction temperature



 $V_o = 1.00 \text{ V}$ ;  $R_s = 0.21 \Omega$ 

(1)  $T_j = 125 \,^{\circ}\text{C}$ ; typical values (2)  $T_j = 125 \,^{\circ}\text{C}$ ; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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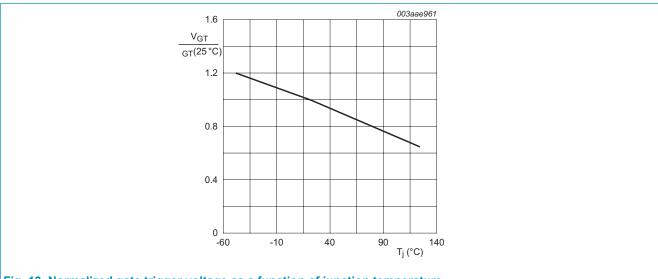


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline

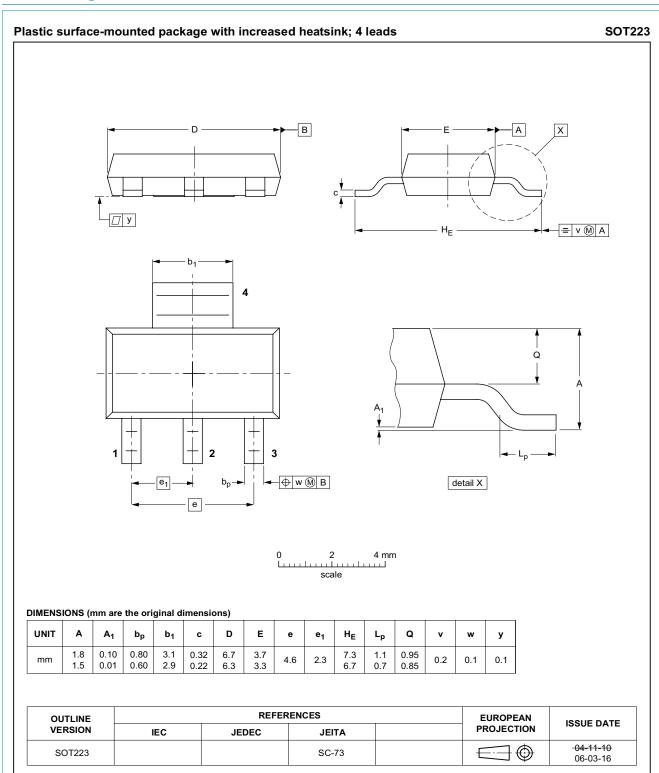
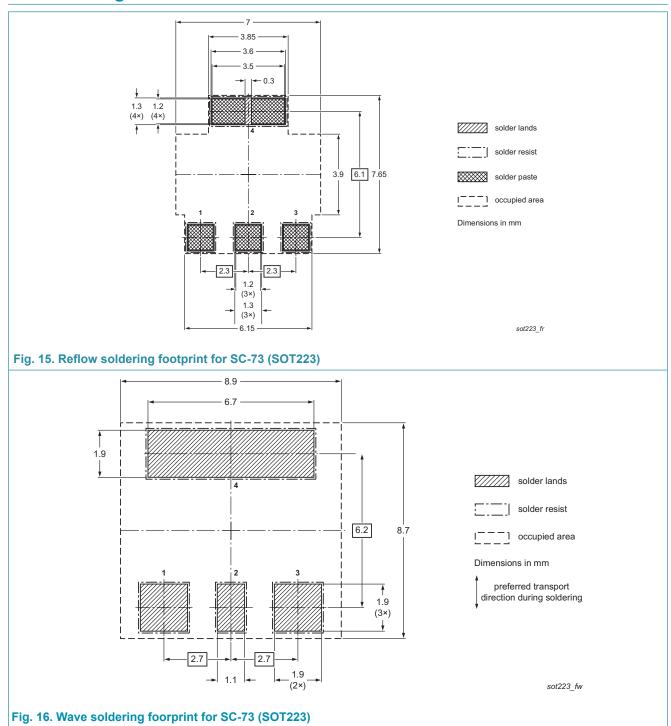


Fig. 14. Package outline SOT223

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# 12. Soldering



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## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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